

GW3AR-20K POWER SPEC

名称	描述	最小值	最大值
UG256内嵌SDRAM封装电源供电要求			
V _{CC}	核电压，LV	0.87V	1.03V
V _{CCIO2/3/4/5/6/7}	I/O Bank2/3/4/5/6/7电源电压	1.14V	3.465V
V _{CCIO0/1}	I/O Bank0/1电源电压，V _{CCIO0/1} 提供SDRAM电压	3.135V	3.465V
V _{CCIO10}	I/O Bank10电源电压	2.375V	3.465V
V _{CCX}	辅助电压	2.375V	3.465V
V _{EFUSE} ^[1]	eFuse写入所需电压	1.62V	1.98V
V _{REFN}	SAR ADC模块参考电压	0V	0V
V _{REFP}	SAR ADC模块参考电压	0V	1.25V
UG256D内嵌DDR2封装电源供电要求			
V _{CC}	核电压，LV	0.87V	1.03V
V _{CCIO0/1/4/5/6/7}	I/O Bank0/1/4/5/6/7电源电压	1.14V	3.465V
V _{CCIO2/3}	I/O Bank2/3电源电压，V _{CCIO2/3} 提供DDR2电压	1.7V	1.9V
V _{CCIO10}	I/O Bank10电源电压	2.375V	3.465V
V _{CCX}	辅助电压	2.375V	3.465V
V _{EFUSE} ^[1]	eFuse写入所需电压	1.62V	1.98V
V _{REFN}	SAR ADC模块参考电压	0V	0V
V _{REFP}	SAR ADC模块参考电压	0V	1.25V
V _{REFDDR}	DDR2参考电压	0.49 x V _{CCIO2/3} V	0.51 x V _{CCIO2/3} V

GW3AR-20K Notes

- Notes:
- 1、 It is recommended that add an ESD protection chip to the JTAG download circuit.
 - 2、 The VCCX value must be set in the GOWIN EDA tool to be consistent with the actual supply voltage.
 - 3、 When VEFUSE is not needed, this power supply can be connected to GND or left floating.
 - 4、 PUDC B=0: All GPIOs except PUDC B have weak pull-up
 - ； PUDC_B=1: All GPIOs have high impedance

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GW3AR-LV20UG256D

